

### Description

The DGTD65T15H2TF is produced using advanced Field Stop Trench IGBT Technology, which provides high-performance, excellent quality, and high ruggedness.

### Features

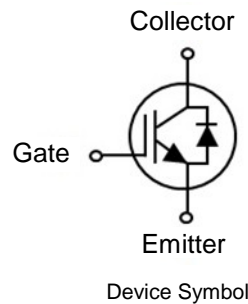
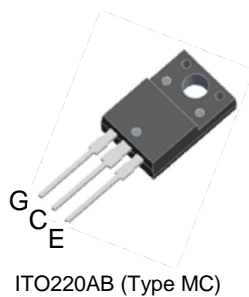
- High Ruggedness for Motor Control
- $V_{CE(sat)}$  Positive Temperature Coefficient
- Very Soft, Fast Recovery Anti-Parallel Diode
- Low EMI
- Maximum Junction Temperature +175°C
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

### Applications

- Motor Drive

### Mechanical Data

- Case: ITO220AB (Type MC)
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Terminals: Finish—Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208
- Weight: 1.9 grams (Approximate)



### Ordering Information (Note 4)

Product	Marking	Quantity
DGTD65T15H2TF	DGTD65T15H2	1000 per Box in Tubes (Note 5)

- Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3).compliant. All applicable RoHS exemptions applied.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.
  5. 50 devices per tube.

### Marking Information



J;| = Manufacturer's Marking  
 DGTD65T15H2 = Product Type Marking Code  
 YY = Year (ex: 18 = 2018)  
 LLLLL = Lot Code  
 WW = Week (01 to 53)

**Absolute Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

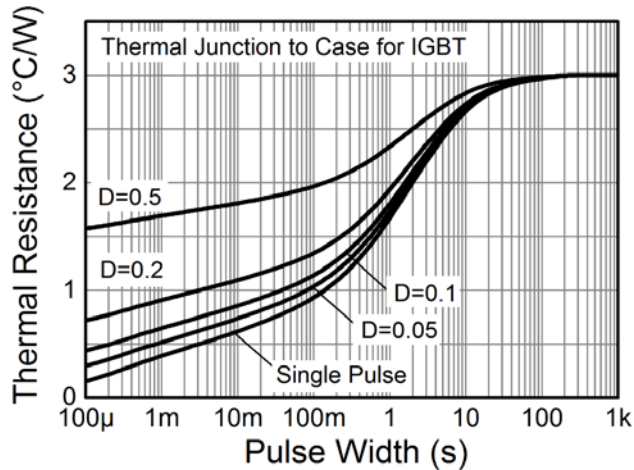
Characteristic	Symbol	Value	Unit
Collector-Emitter Voltage	V <sub>CE</sub>	650	V
DC Collector Current, Limited by T <sub>jmax</sub>	I <sub>C</sub>	T <sub>C</sub> = +25°C	30
		T <sub>C</sub> = +100°C	15
Pulsed Collector Current, t <sub>p</sub> Limited by T <sub>jmax</sub>	I <sub>Cpuls</sub>	60	A
Diode Forward Current Limited by T <sub>jmax</sub>	I <sub>F</sub>	T <sub>C</sub> = +25°C	30
		T <sub>C</sub> = +100°C	15
Diode Pulsed Current, t <sub>p</sub> Limited by T <sub>jmax</sub>	I <sub>Fpuls</sub>	60	A
Gate-Emitter Voltage	V <sub>GE</sub>	±20	V
Short Circuit Withstand Time V <sub>CC</sub> ≤ 360V, V <sub>GE</sub> = 15V, T <sub>j</sub> = +150°C	t <sub>SC</sub>	5	µs

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

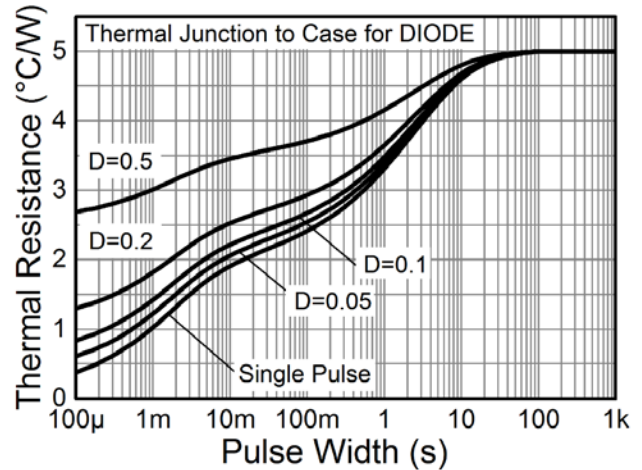
Characteristic	Symbol	Value	Unit
Power Dissipation Linear Derating Factor (Note 7)	P <sub>D</sub>	T <sub>C</sub> = +25°C	48
		T <sub>C</sub> = +100°C	24
Thermal Resistance, Junction to Ambient (Note 6)	R <sub>θJA</sub>	62	°C/W
Thermal Resistance, Junction to Case for IGBT (Note 7)	R <sub>θJC</sub>	3.0	
Thermal Resistance, Junction to Case for Diode (Note 7)	R <sub>θJC</sub>	5.0	
Operating Temperature	T <sub>j</sub>	-40 to +175	°C
Storage Temperature Range	T <sub>STG</sub>	-55 to +150	

Note: 6. For a device mounted in a socket in still air conditions. Collector lead length 10mm.  
7. For a device mounted on a Force Cooled Aluminium Heatsink 80x80x60mm.

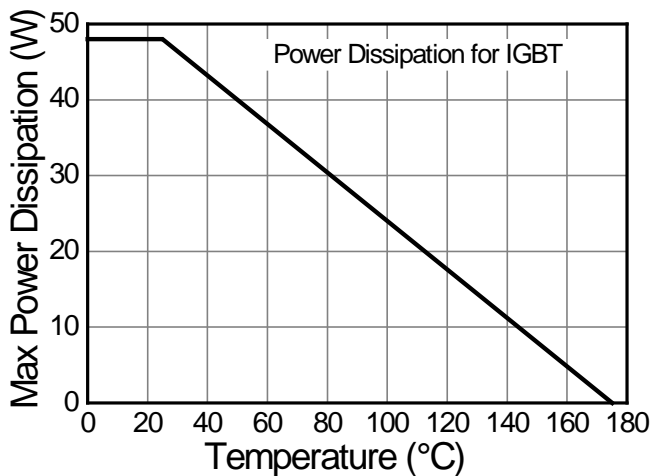
**Thermal Characteristics and Derating Information**



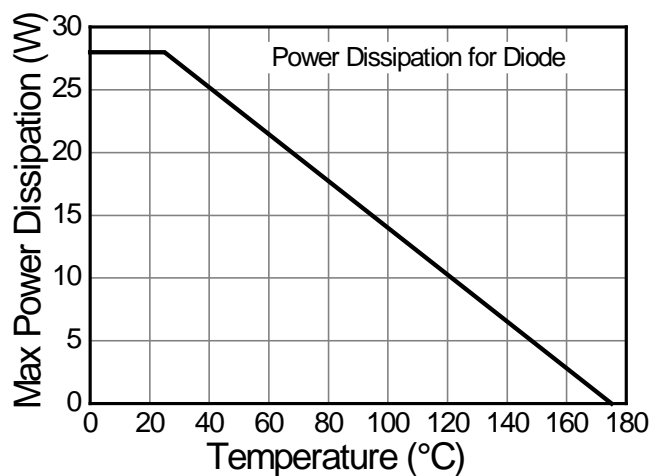
**Transient Thermal Impedance**



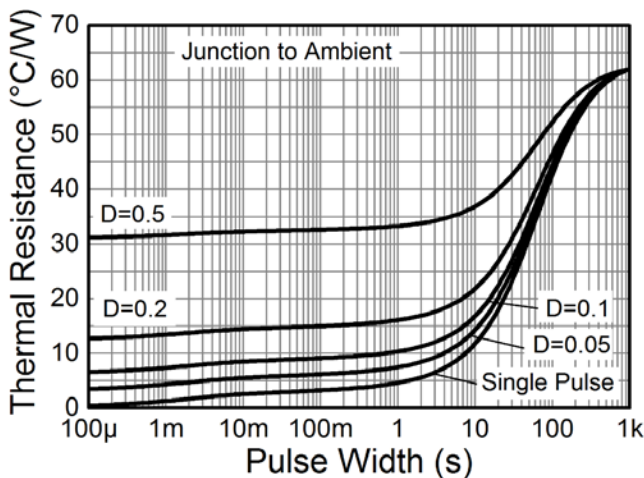
**Transient Thermal Impedance**



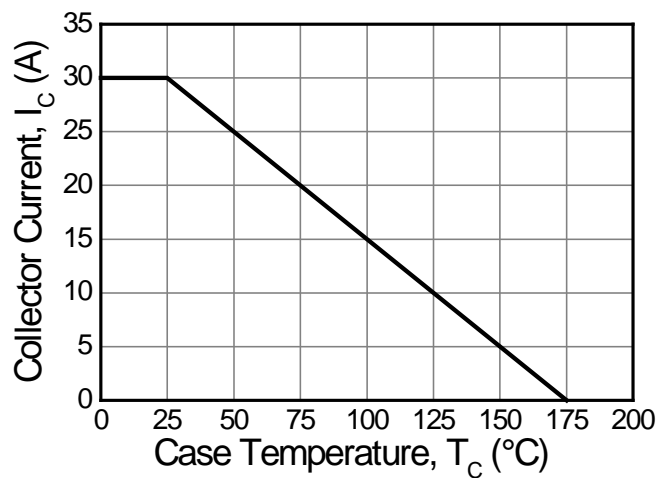
**Derating Curve**



**Derating Curve**



**Transient Thermal Impedance**

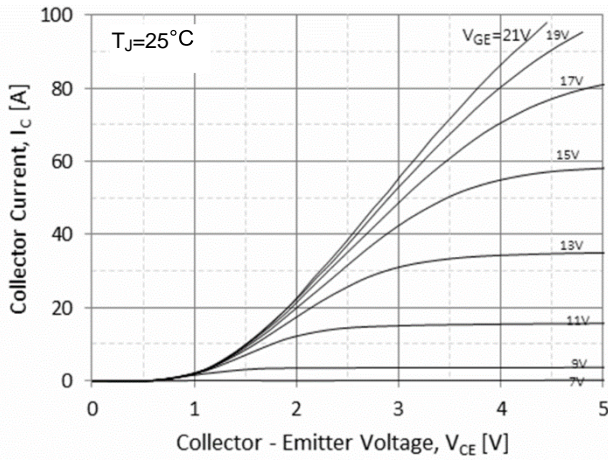


**Case Temperature-Collector Current**

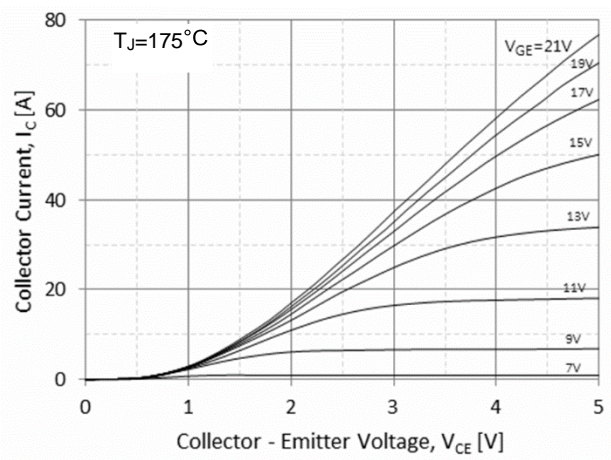
**Electrical Characteristics** (@T<sub>j</sub> = +25°C, unless otherwise specified.)

Parameter	Symbol	Min	Typ	Max	Unit	Condition	
<b>STATIC CHARACTERISTICS</b>							
Collector-Emitter Breakdown Voltage	BV <sub>CEs</sub>	650	—	—	V	I <sub>C</sub> = 2mA, V <sub>GE</sub> = 0V	
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	T <sub>j</sub> = +25°C	—	1.65	2.00	V	I <sub>C</sub> = 15A, V <sub>GE</sub> = 15V
		T <sub>j</sub> = +175°C	—	1.90	—		
Diode Forward Voltage	V <sub>F</sub>	T <sub>j</sub> = +25°C	—	1.85	2.30	V	V <sub>GE</sub> = 0V, I <sub>F</sub> = 15A
		T <sub>j</sub> = +175°C	—	1.95	—		
Gate-Emitter Threshold Voltage	V <sub>GE(th)</sub>	4.5	5.5	6.5	V	V <sub>CE</sub> = V <sub>GE</sub> , I <sub>C</sub> = 0.5mA	
Zero Gate Voltage Collector Current	I <sub>CEs</sub>	—	—	20	μA	V <sub>CE</sub> = 650V, V <sub>GE</sub> = 0V, T <sub>j</sub> = +25°C	
Gate-Emitter Leakage Current	I <sub>GES</sub>	—	—	±100	nA	V <sub>GE</sub> = 20V, V <sub>CE</sub> = 0V	
<b>DYNAMIC CHARACTERISTICS</b>							
Total Gate Charge	Q <sub>g</sub>	—	61	—	nC	V <sub>CE</sub> = 520V, I <sub>C</sub> = 15A, V <sub>GE</sub> = 15V	
Gate-Emitter Charge	Q <sub>ge</sub>	—	11	—			
Gate-Collector Charge	Q <sub>gc</sub>	—	35	—			
Input Capacitance	C <sub>ies</sub>	—	1129	—	pF	V <sub>CE</sub> = 25V, V <sub>GE</sub> = 0V, f = 1MHz	
Reverse Transfer Capacitance	C <sub>res</sub>	—	57	—			
Output Capacitance	C <sub>oes</sub>	—	31	—			
<b>SWITCHING CHARACTERISTICS</b>							
Turn-On Delay Time	t <sub>d(on)</sub>	—	19	—	ns	V <sub>GE</sub> = 15V, V <sub>CC</sub> = 400V, I <sub>C</sub> = 15A, R <sub>G</sub> = 10Ω, Inductive Load, T <sub>j</sub> = +25°C	
Rise Time	t <sub>r</sub>	—	27	—			
Turn-Off Delay Time	t <sub>d(off)</sub>	—	128	—			
Fall Time	t <sub>f</sub>	—	32	—			
Turn-On Switching Energy	E <sub>on</sub>	—	270	—	μJ		
Turn-Off Switching Energy	E <sub>off</sub>	—	86	—			
Total Switching Energy	E <sub>ts</sub>	—	356	—			
Turn-On Delay Time	t <sub>d(on)</sub>	—	17	—	ns		V <sub>GE</sub> = 15V, V <sub>CC</sub> = 400V, I <sub>C</sub> = 15A, R <sub>G</sub> = 10Ω, Inductive Load, T <sub>j</sub> = +175°C
Rise Time	t <sub>r</sub>	—	29	—			
Turn-Off Delay Time	t <sub>d(off)</sub>	—	150	—			
Fall Time	t <sub>f</sub>	—	130	—			
Turn-On Switching Energy	E <sub>on</sub>	—	342	—	μJ		
Turn-Off Switching Energy	E <sub>off</sub>	—	288	—			
Total Switching Energy	E <sub>ts</sub>	—	630	—			
Reverse Recovery Time	t <sub>rr</sub>	—	150	—	ns	I <sub>F</sub> = 15A, di <sub>F</sub> /dt = 200A/μs, T <sub>j</sub> = +25°C	
Reverse Recovery Current	I <sub>rr</sub>	—	5.2	—	A		
Reverse Recovery Charge	Q <sub>rr</sub>	—	390	—	nC		
Reverse Recovery Time	t <sub>rr</sub>	—	207	—	ns	I <sub>F</sub> = 15A, di <sub>F</sub> /dt = 200A/μs, T <sub>j</sub> = +175°C	
Reverse Recovery Current	I <sub>rr</sub>	—	6.1	—	A		
Reverse Recovery Charge	Q <sub>rr</sub>	—	631	—	nC		

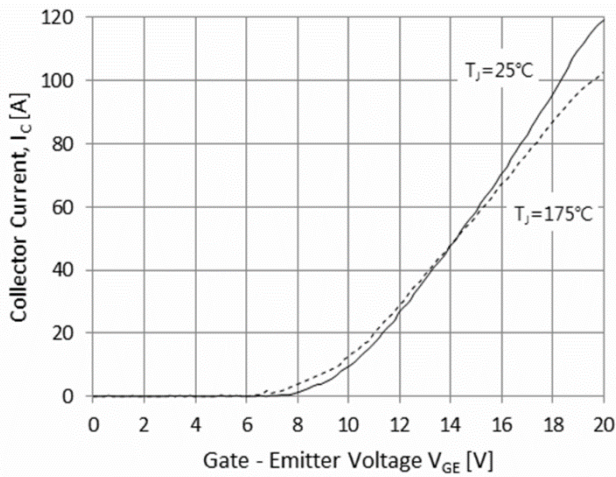
**Typical Performance Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)



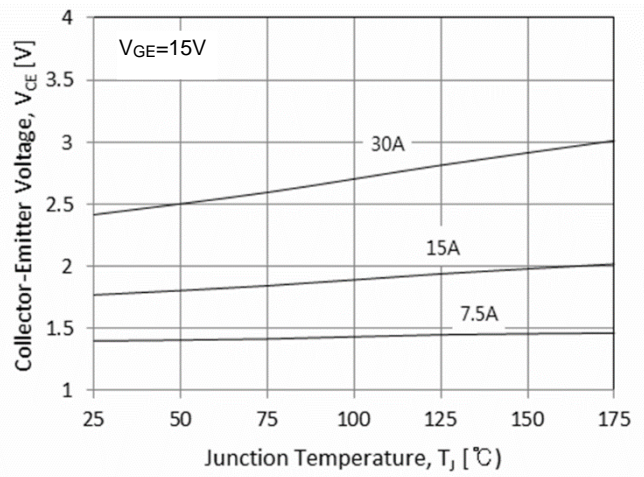
**Fig.1 Typical Output Characteristics ( $T_J = 25^\circ\text{C}$ )**



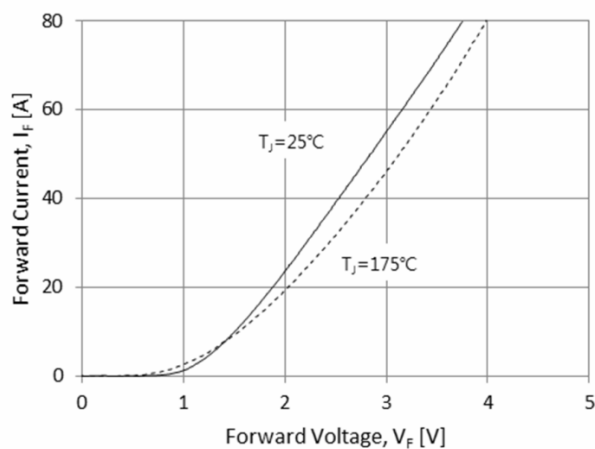
**Fig.2 Typical Output Characteristics ( $T_J = 175^\circ\text{C}$ )**



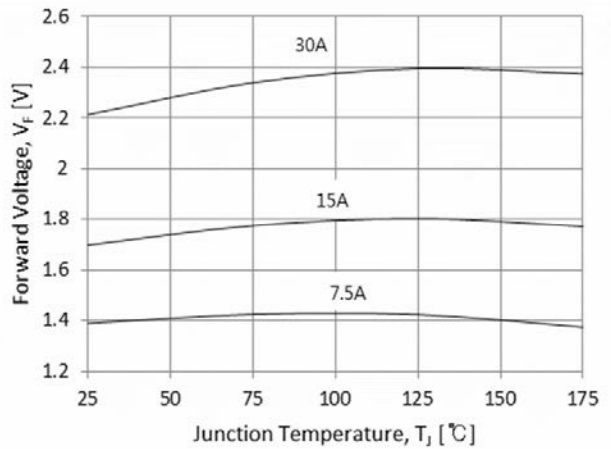
**Fig.3 Typical Transfer Characteristics**



**Fig.4 Typical Collector-Emitter Saturation Voltage - Junction Temperature**

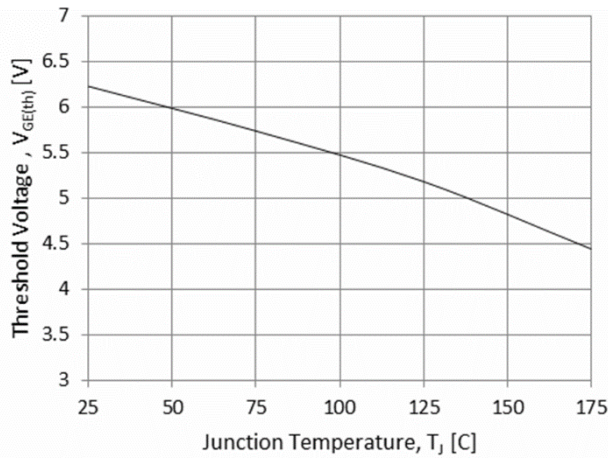


**Fig.5 Diode Forward Characteristics**

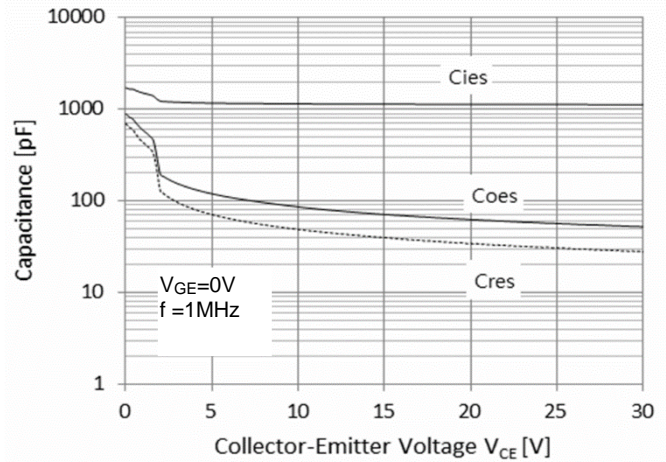


**Fig.6 Diode Forward-Junction Temperature**

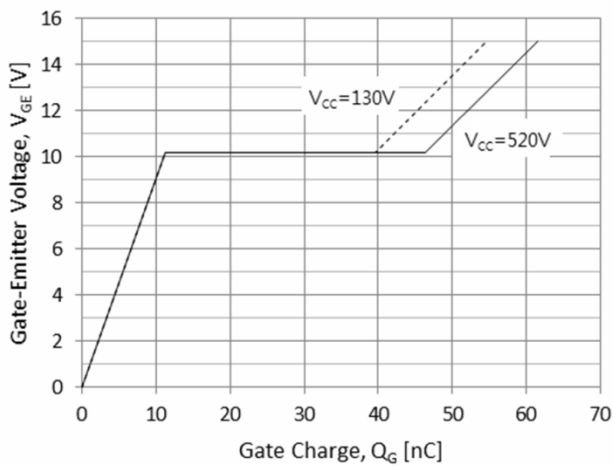
**Typical Performance Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.) (continued)



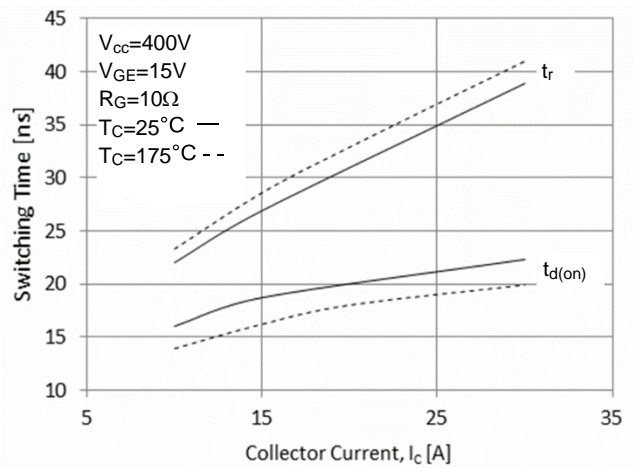
**Fig.7 Threshold Voltage-Junction Temperature**



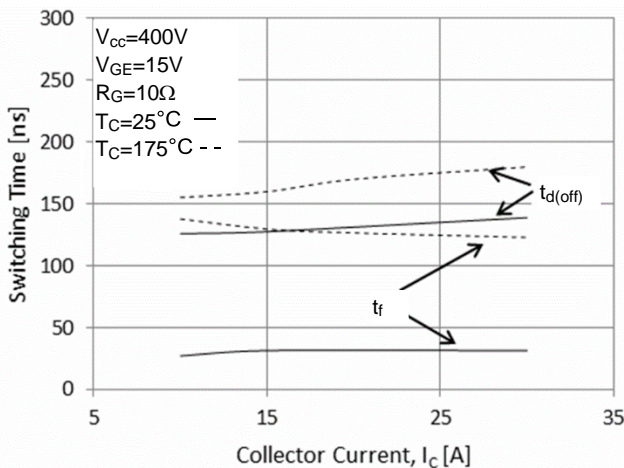
**Fig.8 Typical Capacitance**



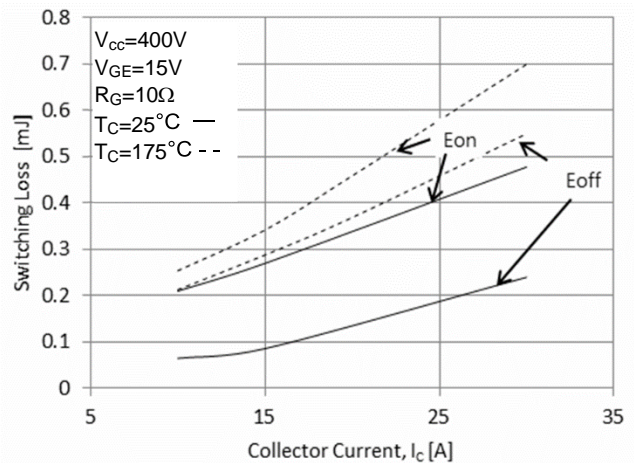
**Fig.9 Typical Gate Charge**



**Fig.10 Typical Turn on-Collector Current**

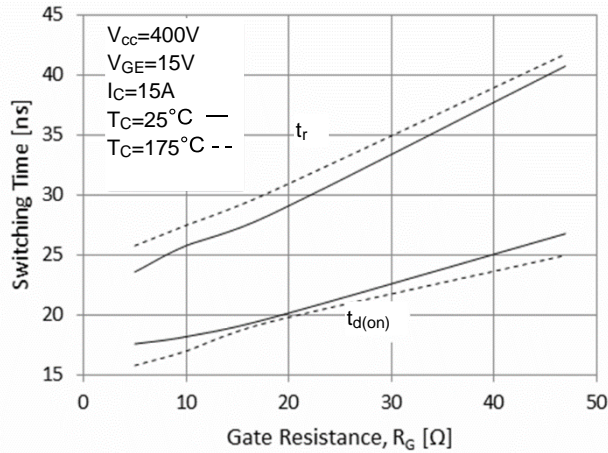


**Fig.11 Typical Turn off-Collector Current**

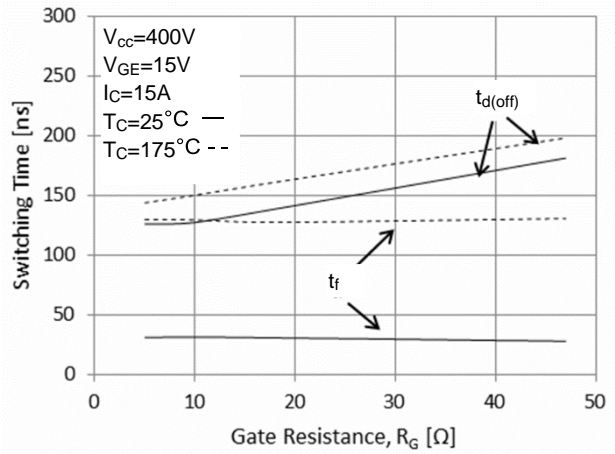


**Fig.12 Switching Loss-Collector Current**

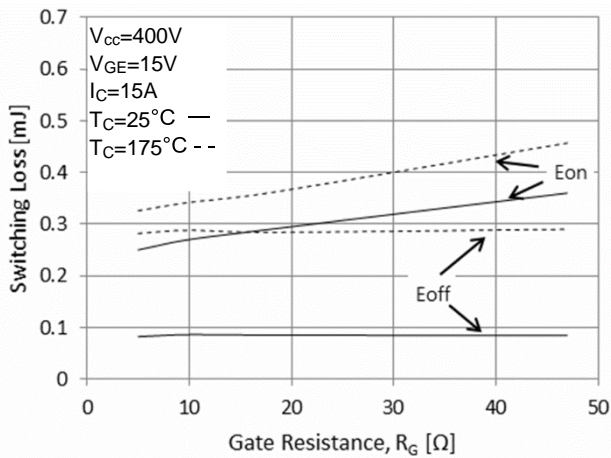
**Typical Performance Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.) (cont.)



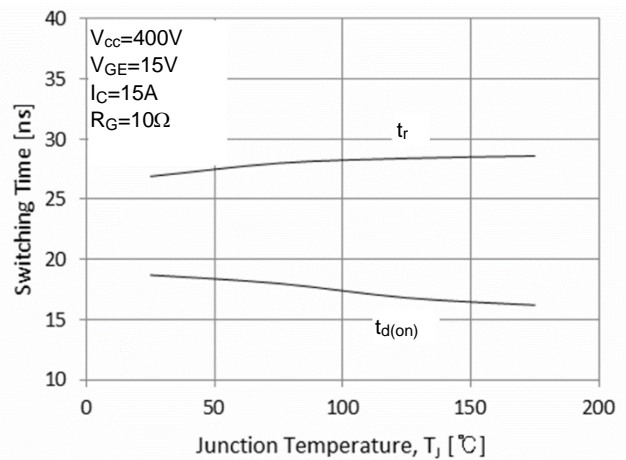
**Fig.13 Turn on Characteristics-Gate Resistance**



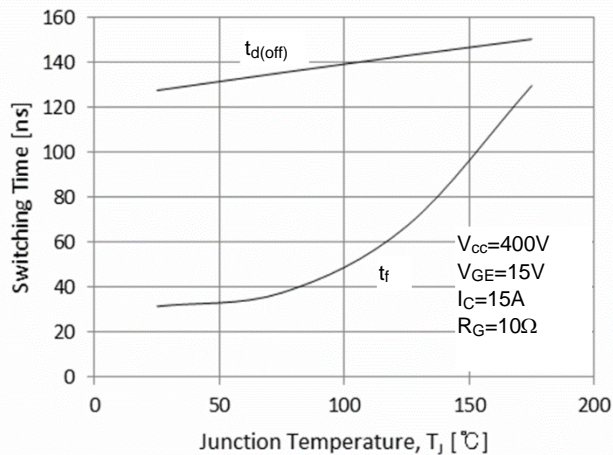
**Fig.14 Turn off Characteristics-Gate Resistance**



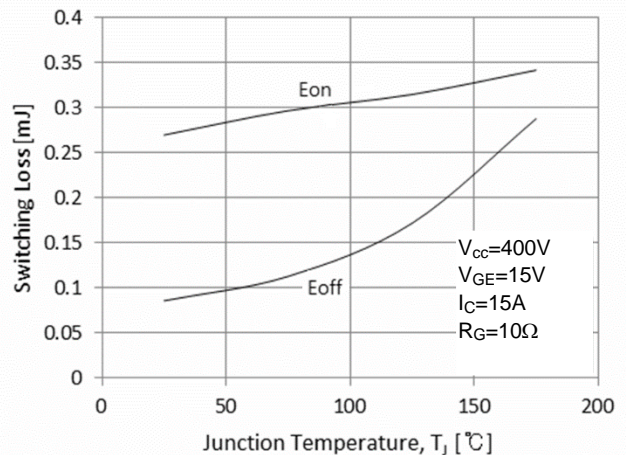
**Fig.15 Switching Loss-Gate Resistance**



**Fig.16 Turn on Characteristics-Junction Temperature**



**Fig.17 Turn off Characteristics-Junction Temperature**

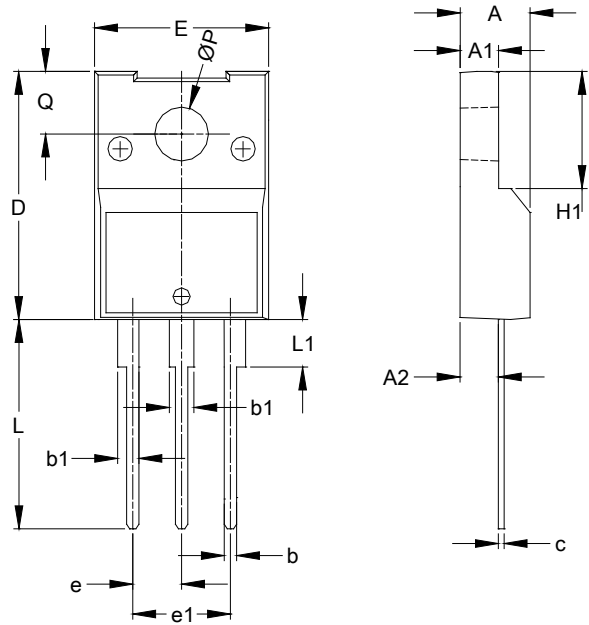


**Fig.18 Switching Loss-Junction Temperature**

**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

ITO220AB (Type MC)



ITO220AB (Type MC)			
Dim	Min	Max	Typ
A	4.30	4.80	—
A1	2.50	3.10	—
A2	2.30	2.90	—
b	0.50	1.00	—
b1	0.95	1.70	—
c	0.40	0.80	—
D	14.50	16.40	—
H1	6.20	7.20	—
E	9.60	10.40	—
e	—	—	2.54
e1	—	—	5.08
L	12.20	14.20	—
L1	2.90	4.70	—
P	3.00	3.40	—
Q	2.40	3.50	—
All Dimensions in mm			

Note : For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device Terminals and PCB tracking.



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